

CX-4

Cryogenic Super Low Noise Amplifier



- Datasheet -

V. 2.7, Jan. 2025

Features:

- Frequency Range approx. 1kHz to 4MHz, model dependent
- Very High Input Impedance
- Super Low Noise (0.31nV/√Hz @ 1MHz, ~4pF=C_{IN, standard version})
- Operation in strong magnetic fields (6T) and low temperatures down to 4.2 K and even lower (options)

Applications:

- Quantum State Readout
- Single Ion FT-ICR
- Tuning Forks
- Schottky Noise Measurements



Attention: Electrostatic Sensitive Device (see hints)

Introduction

The CX-4 is a highly sensitive voltage preamplifier, intended for low-temperature, low-noise applications. The circuit can be used directly inside a cryogenic vacuum setup. Cryogenic GaAs (Gallium-Arsenide)-FET technology allows for deep-cryogenic operation, even in strong magnetic fields up to several Tesla (optional), as they are present in NMR, FT-ICR or solid-state research applications. The amplifier module covers a frequency range of approx. 4kHz....4MHz and has very high input impedance. The latter is suited specially for sensing induced image currents (slow ions, tuning forks) or for semiconductor noise measurements. The ultra-low input voltage noise around 310pV/√Hz around 1MHz is quite outstanding and represents the state-of-the art technology for high-impedance amplifiers with low input capacitance. Please note our remarks about usage in a high B-field, below.

The module is delivered as print board-stack with aluminum lids and comes together with a mating room temperature biasing controller. Bias- and signal lines can be connected by normal soft-soldering procedures by the user. The device is available as 1- or 2-channel version. Also, a low-frequency version (option LF) is available with improved low-frequency behavior around and below 10kHz. For high frequency version (30MHz) see separate datasheet.

Application Example

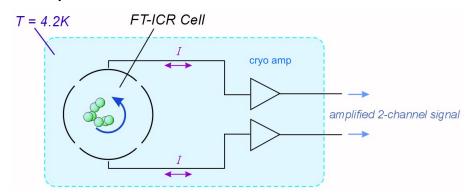


Fig. 1: Typical Application: High Impedance Signal Detection in FT-ICR Cells

Solder Connections / Pinout



Fig. 2a: Pinout / Solder Pad Connections, 2-channel version, and recommended external B-field orientation in terms of direction and polarity, in case of very high external B-fields. Left picture: standard variant, center picture 'narrow-case' version without temperature sensor. Right picture: dual channel SMA output version, rear side view Pins: 1 = Temperature Sensor, 2 = GND, 3 = G1B, 4 = G1A.

Fig. 2b Single channel version with SMA connectors



Electrostatic Sensitivity



This device can be **damaged** by ESD (Electrostatic Discharge). It is **strongly recommended** to handle the device with appropriate precaution. Failure to observe proper handling and installation procedures can cause serious damage. This ESD damage can range from subtle performance degradation to complete device failure.

Practical Hints:

Whenever the device is picked up by hand, ensure that the ground pin or aluminium case is touched <u>first</u> before touching any other pin. Touching any other pin than ground first, **may destroy this device**. Similar precaution has to be applied when changing the location of the device: Most important the destinations ground has to be on the same potential as the devices ground (ground balancing). Therefore, connect both grounds first (using a resistor around 100kOhm, or simply by hand without gloves) before making any other connection or changing the amplifier position. Failure to perform ground balancing may easily lead to severe **irreversible damage** of the device. Always ensure to take thorough measures to avoid static charges building up in the vincinity of this device or laboratory equipment connected to it. Furthermore, **beware of non-grounded Soldering Irons**: Inexpensive Soldering Irons often have floating solder tips, which easily may **destroy** ESD-sensitive parts.

Connection to Room Temperature Biasing Controller

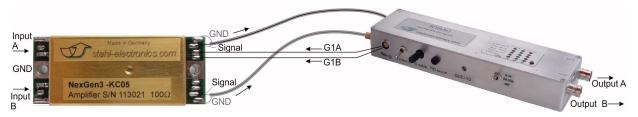


Fig. 3 Cabling to Room Temperature Biasing Controller Unit A3-5 (2-channel version)

As indicated in the picture above, the device is connected to its mating room temperature controller through two biasing lines (G1A, G1B) and the output signal lines (coaxial lines preferred). G1A and G1B are negative supplies (typical values for G1A, G1B are -25mV at cryogenic temperatures) and will be regulated by the Biasing Controller.

Absolute Maximum Ratings

Note: Stress above these ratings may cause permanent damage or degradation of device performance. Exceeding these conditions for extended periods may also degrade device reliability.

| Quantity | Limits | | Remarks | |
|---|--------|--|--|--|
| | min. | max. | | |
| neg. Supply Voltage G1A/B | +1.0V | -10V | | |
| Input Voltage absolute value (AC+DC) AC | | 100 V_{pk} vs. GND, $3V_{pp}$, $f = 0 5MHz$ | derating inversely proportional with frequency above 5MHz | |
| Input Current | | 40mA _{eff} | continuous current through protection circuitry | |
| Output Voltage | -0.3V | +4V | Under normal conditions no voltage source must be applied to the outputs. | |
| Storage Temperature | 3.5K | 125°C | | |
| Storage Humidity | | 65% @ 40°C | | |
| Cool-down Rate, Heating Rate | | +/- 20K / minute | Care has to be taken during cool down and warm up phases. A sudden drop into cryogenic liquids may destroy the device. | |

Table 1: Absolute Maximum Ratings

Cleaning and Baking

The CX-4 device may be carefully purged from organic attachements by rinsing with a mild solvent. Ethanol or isopropanol are acceptable. It may be also dipped for a while into these solvents. Stronger solvents like acetone are <u>not</u> recommended. Due to sensitive internal parts (thin bond wires of approx. only 40µm Gold thickness), in <u>no case</u> pressurised air or pressured solvents must be guided into the inner parts of the device. Ultrasound cleaning is not recommended. Baking is possible up to 125°C, and should not last longer than 48 hours prior to use at cryogenic temperatures.

Characteristic Data and Operating Parameters Cryogenic Amplifier CX-4 in conjunction with mating Room Temperature Biasing Controller Unit A3-5

| Biasing Conroller Unit 60 $\Omega \pm 10\%$ Input Noise T = 300K voltage noise density 12 nV/ \sqrt{Hz} f = 100 kHz 500 kHz 3.3 nV/ \sqrt{Hz} 1 MHz 4 MHz 7 = 4.2K voltage noise density | in conjunction with mating Room Temperature Biasing Controller Unit A3-5 | | | |
|--|--|---------------------------------------|--|--|
| 2 kHz4 MHz (standard version) 390 Hz3 Z MHz (low frequency version) 490 Hz3 Z MHz (low frequency version) 190 Hz3 Z MHz (low frequen | | typical Value | Remarks/Conditions | |
| (standard version) 390 Hz3.2 MHz (low frequency version) 390 Hz3.2 MHz (low frequency version) possible. For high frequency version f = 100kHz possible. Tor high frequency version f = 100kHz | | | | |
| 390 Hz3 2 MHz continue | for ±3dB deviation | | | |
| Cain | | | | |
| Gain linear voltage gain @ T = 4.2K, | | | | |
| Ininear voltage gain @ T = 4.2K, | | (low frequency version) | see separate datasheet. | |
| $\begin{array}{c ccccccccccccccccccccccccccccccccccc$ | | 050) (0 () 0 50 (| f = 100kHz | |
| $ \begin{array}{c} \text{(for elevated temperatures} > 4.2 \text{K see} \\ \text{data at end of this document)} \\ \text{Remark:} \\ \text{linear voltage gain @ T = 300K} \\ \text{Remark:} \\ \text{linear voltage gain @ T = 300K} \\ \text{Gain Mismatch} \\ \text{between both cannels} \\ \text{Input Impedance vs. GND at either input} \\ \text{DC, T = 4.2K 300K} \\ \text{AC, 300K} \\ \text{AC, 4.2K} \\ \text{input capacitance vs. GND} \\ \text{Input capacitance vs. GND} \\ \text{Dynamic Output Impedance} \\ \text{corpolite of 10} \\ \text{max. AC Output Power} \\ \text{T = 300K} \\ \text{Yoltage noise density} \\ \text{T = 4.2K} \\ \text{voltage noise density} \\ \text{T = 4.2K} \\ \text{voltage noise density} \\ \text{T = 4.2K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 4.2K} \\ \text{Input Noise} \\ \text{T = 4.2K} \\ \text{Input Noise} \\ \text{T = 300K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 4.2K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 4.2K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 4.2K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 300K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 300K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 300K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ \text{T = 300K} \\ \text{Voltage noise density} \\ \text{Input Noise} \\ $ | | | 1 - 100KHZ | |
| (for elevated temperatures >4.2K see data at end of this document) Remark: linear voltage gain @ T = 300K Gain Mismatch between both cannels Input Impedance vs. GND at either input DC, T = 4.2K 300K AC, 300K AC, 4.2K input capacitance vs. GND Dynamic Output Impedance vs. GND Dynamic Output Impedance ws. GND Expected Impedance Biasing Conroller Unit Biasing Conroller Unit T = 4.2K 300K AC 300 N/Hz 3 mW Expected Impedance Biasing Conroller Unit T = 4.2K 300K 12 nV/NHz 6 nV/NHz 13 nV/NHz 10 nV/NHz | 4 steps | | over-all amplification including biasing | |
| Remark: linear voltage gain @ T = 300K approx. factor of 4 smaller than at 4.2K (standard version), or factor of 10 smaller than at 4.2K (standard version) Gain Mismatch between both cannels typ. 1.5% T = 4.2K, f = 30kHz 1MHz Input Impedance vs. GND at either input DC, T = 4.2K 300K AC, 300K AC, 4.2K > 40MΩ capacitively coupled > 15MΩ f < 100kHz | (for elevated temperatures >4.2K see | | | |
| 1.0 max voltage gain @ T = 300K 4.2k (standard version), or factor of 10 smaller than at 4.2k ((low frequency version) T = 4.2k, f = 30kHz 1MHz | | x 2400 V/V ± 8% | 4 amplification steps are available. | |
| 1.0 max voltage gain @ T = 300K 4.2k (standard version), or factor of 10 smaller than at 4.2k ((low frequency version) T = 4.2k, f = 30kHz 1MHz | Domorks | annual factor of A annual anthon of | | |
| 10 smaller than at 4.2K (low frequency version) T = 4.2K, f = 30kHz 1MHz | | | | |
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| Input Impedance vs. GND at either input DC, T = 4.2K 300K AC, 4.2K input capacitance vs. GND AC, 300K AC, 4.2K input capacitance vs. GND Dynamic Output Impedance cryogenic stage @ 4.2K max. AC Output Power Expected Impedance Biasing Conroller Unit Input Noise T = 300K T = 4.2K Input Noise T = 300K Input Noise T = 300K Input Noise T = 4.2K Input Noise T = 300K Input Noise T = 4.2K Input Noise Input Noise Input Noise T = 300K Input Noise In | Gain Mismatch | | T - 1 2K f - 30kU- 1MU- | |
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| either input DC, T = 4.2K 300K AC, 300K AC, 4.2K input capacitance vs. GND Dynamic Output Impedance cryogenic stage ② 4.2K max. AC Output Power Expected Impedance Bliasing Conroller Unit Input Noise T = 300K voltage noise density T = 4.2K voltage noise density standard version 1.0 nV/√Hz 0.35 nV/√Hz 0.31 nV/√Hz 0.5 nV/√Hz 0.5 nV/√Hz 0.5 nV/√Hz 1 MHz 1 | DOLWCON DOWN CANNIENS | | | |
| either input DC, T = 4.2K 300K AC, 300K AC, 4.2K input capacitance vs. GND Dynamic Output Impedance cryogenic stage ② 4.2K max. AC Output Power Expected Impedance Bliasing Conroller Unit Input Noise T = 300K voltage noise density T = 4.2K voltage noise density standard version 1.0 nV/√Hz 0.35 nV/√Hz 0.31 nV/√Hz 0.5 nV/√Hz 0.5 nV/√Hz 0.5 nV/√Hz 1 MHz 1 | Input Impedance vs. GND at | | | |
| DC, T = 4.2K 300K | | | | |
| AC, 300K AC, 4.2K capacitively coupled >16MΩ f < 1kHz f < 100kHz f < 100kHz input capacitance vs. GND t.17pF ±1.0pF standard version 117pF ±7.0pF LF version Dynamic Output Impedance cryogenic stage ② 4.2K | | > 40MO | | |
| input capacitance vs. GND $A.2pF \pm 1.0pF$ standard version $A.2pF \pm 1.0pF$ LF version $A.2pF$ LF | | | f < 1kHz | |
| input capacitance vs. GND 4.2pF ±1.0pF standard version 117pF ±7.0pF LF version Dynamic Output Impedance cryogenic stage @ 4.2K max. AC Output Power 4 kΩ ± 25% 5 max. AC Output Power 5mW Expected Impedance Biasing Conroller Unit Input Noise T = 300K voltage noise density 12 nV/√Hz 6 nV/√Hz 3.3 nV/√Hz 1 MHz 3.0 nV/√Hz 4 MHz T = 4.2K voltage noise density standard version 1.0 nV/√Hz 0.35 nV/√Hz 1 MHz 0.35 nV/√Hz 1 MHz | | | | |
| 117pF ±7.0pF | , | capacitively coupled = 15ivisz | | |
| 117pF ±7.0pF | input capacitance vs. GND | 4 2nF +1 0nF standard version | T = 4.2K 300K | |
| Dynamic Output Impedance cryogenic stage @ 4.2K | ··· | | | |
| cryogenic stage @ 4.2K | Dynamic Output Impedance | 117 pt ±1.0pt Lt version | | |
| max. AC Output Power 3 mW Expected Impedance Biasing Conroller Unit Input Noise T = 300K voltage noise density 60 Ω ± 10% 12 nV/√Hz 6 nV/√Hz 3.3 nV/√Hz 3.3 nV/√Hz 3.0 nV/√Hz 1 MHz 4 MHz f = 100 kHz 500 kHz 1 MHz 4 MHz T = 4.2K voltage noise density standard version 1.0 nV/√Hz 0.45 nV/√Hz 0.35 nV/√Hz 0.31 nV/√Hz 0.5 nV/√Hz f = 30 kHz 100 kHz 500 kHz 1 MHz 4 MHz Iow-frequency version (LF) 7.0 nV/√Hz 2.5 nV/√Hz 1 nV/√Hz 4 00pV/√Hz f = 300 Hz 1 kHz 3 kHz 10 kHz 10 kHz | | 4 kO + 25% | f = 100kHz | |
| Expected Impedance Biasing Conroller Unit Input Noise $T = 300K \text{ voltage noise density}$ $12 \text{ nV}/\sqrt{\text{Hz}}$ $6 \text{ nV}/\sqrt{\text{Hz}}$ $3.3 \text{ nV}/\sqrt{\text{Hz}}$ $3.0 \text{ nV}/\sqrt{\text{Hz}}$ $1.0 \text{ nV}/\sqrt{\text{Hz}}$ $0.45 \text{ nV}/\sqrt{\text{Hz}}$ $0.35 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.5 \text{ nV}/\sqrt{\text{Hz}}$ 1 MHz | eryegerne etage @ n.z.r | + K22 ± ZO /0 | 1 100Ki i2 | |
| Expected Impedance Biasing Conroller Unit Input Noise $T = 300K \text{ voltage noise density}$ $12 \text{ nV}/\sqrt{\text{Hz}}$ $6 \text{ nV}/\sqrt{\text{Hz}}$ $3.3 \text{ nV}/\sqrt{\text{Hz}}$ $3.0 \text{ nV}/\sqrt{\text{Hz}}$ $1.0 \text{ nV}/\sqrt{\text{Hz}}$ $0.45 \text{ nV}/\sqrt{\text{Hz}}$ $0.35 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.31 \text{ nV}/\sqrt{\text{Hz}}$ $0.5 \text{ nV}/\sqrt{\text{Hz}}$ 1 MHz | max. AC Output Power | 3 mW | | |
| Biasing Conroller Unit 60 Ω ± 10% Input Noise 12 nV/√Hz f = 100 kHz T = 300K voltage noise density 12 nV/√Hz 500 kHz 3.3 nV/√Hz 1 MHz 4 MHz T = 4.2K voltage noise density 1.0 nV/√Hz f = 30 kHz 0.45 nV/√Hz 100 kHz 500 kHz 0.35 nV/√Hz 1 MHz 500 kHz 1 MHz 1 MHz 4 MHz Iow-frequency version (LF) 7.0 nV/√Hz f = 300 Hz 1 nV/√Hz 1 kHz 3 kHz 400pV/√Hz 10 kHz | • | - | | |
| Input Noise $T = 300K$ voltage noise density 12 nV/ \sqrt{Hz} 6 nV/ \sqrt{Hz} 500 kHz 500 kHz 3.3 nV/ \sqrt{Hz} 1 MHz 4 MHz 1 MHz 4 MHz 7 1 MHz 1 1 0 nV/ \sqrt{Hz} 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 | Expected Impedance | | max. AC Output Power 5mW | |
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| 6 nV/√Hz 500 kHz 3.3 nV/√Hz 1 MHz 4 MHz 3.3 nV/√Hz 4 MHz 50.45 nV/√Hz 100 kHz 500 kHz 100 kHz 500 kHz 100 kHz 500 kHz 100 kHz 500 kHz 1 MHz 1 mV/√Hz 1 mV/mV/mZ 1 mV/ | Input Noise | | | |
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| $\begin{array}{cccccccccccccccccccccccccccccccccccc$ | | | | |
| $\begin{array}{cccccccccccccccccccccccccccccccccccc$ | standard version | 1.0 nV/√Hz | | |
| $\begin{array}{cccccccccccccccccccccccccccccccccccc$ | | | | |
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| $\begin{array}{cccccccccccccccccccccccccccccccccccc$ | | | | |
| Iow-frequency version (LF) | | | 4 MHz | |
| 2.5 nV/√Hz 1 kHz 1 nV/√Hz 3 kHz 400pV/√Hz 10 kHz | | | | |
| 2.5 nV/√Hz 1 kHz 1 nV/√Hz 3 kHz 400pV/√Hz 10 kHz | low-frequency version (LF) | 7.0 nV/√Hz | f = 300 Hz | |
| 1 nV/√Hz 3 kHz 400pV/√Hz 10 kHz | | | | |
| 400pV/√Hz 10 kHz | | | 3 kHz | |
| | | | | |
| 210001112 | | | 100 kHz | |
| | | 2.000/11/2 | | |

| continued | | | |
|--------------------------------|--|---|--|
| current noise density | | | |
| standard version | 6.5 fA/√Hz, T = 4.2K | f = 100 kHz | |
| | | | |
| low-frequency version (LF) | 4.5 fA/√Hz, T = 4.2K | f = 100 Hz to 10 kHz | |
| Operating voltages | | | |
| positive supply voltage on | +0.25 V | | |
| signal line | 10.23 V | Positive and negative supply should be | |
| olgital into | | provided by a room temperature | |
| G1A, G1B negative bias | -0.1V to -3.0 V @ 300 K | biasing unit | |
| voltage | - 25mV to -75mV @ 4.2 K | Ĭ | |
| Supply Currents @ 300K4.2K | • | | |
| positive supply on signal line | 1.6 mA each channel | | |
| negative supply current G1A/B | < 15 µA | | |
| Operating Temperatures | T = 4.2 K 77K and 300 K | The device is primarily designed for | |
| | | low temperature applications | |
| Applicable external | B = 0 to 100mT, | external field must be in parallel to the | |
| magnetic field B | optional to 6T (contact manufacturer) | long-side of the device (+/-10°) at | |
| | | fields up to B = 0.1T and deviate no more that +/-2° above 0.1T. | |
| | | Orientation like shown in fig. 2 (check | |
| | | also B polarity) | |
| Magnetic Properties | Device consists mostly of non- | In conjunction with FT-ICR cells, it is | |
| magnette i reperties | magnetic materials. | recommended to locate the device | |
| | Spurious amounts of ferromagnetic | min. 5cm away in order to avoid | |
| | substances < 5 x 10 ⁻³ gr. are possible | magnetic disturbance | |
| Size CX-4 1-ch., and narrow- | 40.5mm x 16mm x 8.9mm | | |
| case 2-channel | | | |
| Size CX-4 2-ch. | 54.5mm x 21.2mm x 8.9mm | | |
| D T | 040 05 04 | | |
| Room Temperature Biasing Unit | approx. 210mm x 65mm x 34 mm | | |
| Outgassing | (to be determined) | | |
| Weight Cryogenic Unit | approx. 25 gr. | | |
| Room Temperature Controller | 400 gr. | | |
| Power Supply for | Output +/-5V on Lemo Connector | Attention: external B-field at location, | |
| Room Temperature Biasing | 3-pole 0B-style | the mains adaptor is placed, must not exceed B = 10mT to prevent damage or | |
| | | fire hazard. | |
| | | | |

Table 2: Characteristic Data

Required External Circuitry

The cryogenic CX-4 amplifier requires biasing lines, which should be adjusted to hold the device at stable working conditions. The room temperature controller (e.g. Type A3-5), which is provided along with the cryogenic amplifier, regulates these bias lines (G1A/B for channels A and B, or a single Gate line in case of a 1-channel CX-4) to be around -25mV at 4.2K environmental temperature, by means of an automatic PID regulation loop. For testing purposes one can also disable the regulation and set values manually (optional knob on front side of amplifier). Increasing (making more positive) these values leads to an increase of current consumption, which is normally around 1.6mA each channel and vice versa.

The biasing controller of the CX-4 serves also as a tool for error finding and debugging. Also, the controller provides further AC amplification in discrete steps, normally set to x 250 V/V, x 600 V/V, x 1200 V/V or x 2400 V/V of voltage amplification at 50 Ohm load (about twice as much on high impedance load). In case of two channels, it also supports a differential operation, by building the signal difference between the two channels (see also figure 7). In this mode, signals being common to both channels are suppressed by typically 2 orders of magnitude with respect to their amplitude.

Figure: 4: the roomtemperature controller indicates the status of the cryo amplifier and allows for setting the overall-amplification factor. The stated values of amplification factors refer to cryogenic operation and 50 Ohm

GND termination at the roomtemperature controller outputs.

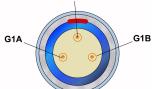


Figure 5: Pinout of connector socket (Lemo 0B type) at the side of the room-temperature controller for providing bias lines to the cryogenic CX-4 amplifier.

A connection cable is provided by the manufacturer, to connect this Biasing output socket to a vacuum flange towards the cryogenic amplifier. The open ends of this cable should be mounted in an electrically shielded way to corresponding feedtrough pins. The 3 open wires are normally G1A (brown), GND (white) and G1B (green). Please check the labelling marks on the cable isolation.

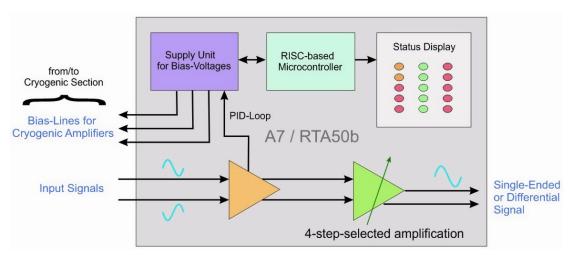


Figure 6: Block diagram of 2-channel roomtemperature controller

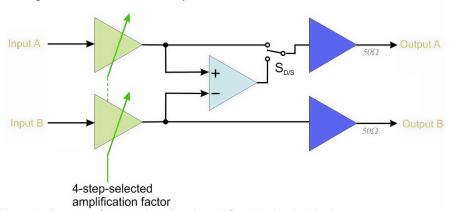
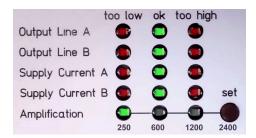


Figure 7: Schematic diagram of the analog signal amplifier circuitry inside the roomtemperature controller. The mode switch $S_{\text{Dual/Differential}}$ allows for choosing between dual-channel or differential operation

Monitoring section

This section consists mainly of a microcontroller and an attached LED (light emitting diode) status display. The microcontroller makes use of instrumentation amplifiers inside the supply unit and observes the biasing currents and voltages once a cryogenic amplifier is connected. This information



is processed and the results are displayed on a LED-display, such that an overview of the cryogenic amplifier's status is obtained. Eventual problems in the cryogenic region are therefore easier to locate.

Figure 8:

LEDs indicate the status of biasing lines, assisting to find problems in the cryogenic region. The bottom row represents the amplification factor, and the amplification selection switch. Pressing the switch increases the amplification factor, a long press resets to the minimum value.

The threshold levels, upon which the LEDs change their status, are set by default (software programming) to the values stated in the Appendix. In normal operation all light up green.

Connections inside Vacuum

Attention:

When mounting cables and lines to the CX-4 amplifier, always observe ESD handling hints (see page 3)

Biasing Lines

The 2 Biasing lines G1A and G1B carry just minor currents and can therefor be implemented as thin isolated wires, e.g. made of Constantan[™] or Manganin[™], to ensure low thermal conductivity to avoid thermal load on the cryogenic part of a setup. Cryo coax lines could be used as well.

AC connections to Room Temperature

The signal connection from cryogenic to room temperature (Output A, Output B) should be implemented as (preferably: short) coaxial lines, in order to minimize external interference and the possibility of unwanted feedback from the output to the high-impedance input. Cable impedance of the room temperature connection is not critical, unless the cable length greatly exceeds ~2m. A cryogenic low-capacitance cable is preferable.

Input Connections and Grounding, Risk of Self-Oscillations

Using high impedance amplifiers, such as the CX-4, requires proper *Grounding and Shielding* at the input side. A thorough grounding and shielding is essential to maintain good device performance and low noise characteristics, and to avoid the creation of parasitic oscillations. Typical RF (radio frequency) -design rules for proper grounding and shielding apply here, even though the upper limit of the frequency range just barely reaches the HF (high frequency) regime. To ensure a "clean" electrical environment provide good ground connections especially around the amplifier input. The gounding



hole at the input (see photo) may serve as central connection point, to which the signal ground may be connected. All lines from the signal source to the amplifier's inputs should be kept as short as possible and of low inductance-style (no large loops or spirals).

Figure 9: Illustration of connecting a sample to the amplifier's inputs.

Very short silver-plated wires represent the electrical signal connection while a Brass or Aluminium screw

establishes a tight mechanical GND contact to a well-conducting substrate. In the cold state, the Brass/Aluminium screw will stay tight, other material may not.

Please note that insufficient grounding or shielding around the signal source, may lead to a considerably increased noise level and furthermore increases the risk of self-oscillations. These uncontrollable oscillations appear typically at MHz- frequencies and are normally an indication of insufficient shielding at the input. Also note that the supply lines of the preamplifier should be free of noise before reaching this device. In very noisy environments, this can be achieved by filtering the bias voltages G1A, G1B through RC lowpasses, consisting of R (approx. $10k\Omega$ to $50k\Omega$) and C of approx. 10nF (with plastic dielectric, or NPO type, **not** X7R or Z5U type) to GND.

External Magnetic Field

In case a static external magnetic field is applied (e.g. FT-ICR or NMR/MRI setups) the CX-4 amplifier must be oriented like shown in figure 2, i.e. with the long side parallel to the external field, max. 2 degrees deviation at B-fields above 0.1T. Also, the polarity is decisive and thus the field orientation matters. This applies for magnetic fields higher than about 0.1T. In case magnetic fields larger 0.1T are used, please contact manufacturer for special chip alignment of parts inside the amplifier casing. Figure 2 depicts the proper orientation and refers to the usual convention of polarity definition, i.e. the field line arrow points from a magnetic north pole to a magnetic south pole. For instance, earth's geographic North Pole is a magnetic south pole; a conventional mechanical compass or Smart Phone App may be therefore used, to determine the magnetic field direction at a given experimental setup, at safe distance from a strong magnet.

Input Circuitry

The subsequent figure illustrates the input protection circuitry for each input. DC blocking capacitors are provided in order to maintain a reasonable amount of admissible DC offset voltage being applied to the inputs without harm. These blocking capacitors C_{blocking} are located outside the upper aluminium housing (see figure) and can be bridged / removed in favour of zero-ohm resistors for an optimised noise figure or in case a different coupling scheme is required. In case they are kept in place, the maximum allowed offset voltage at each input is +/-100V versus GND.

The limited pulse capability of maximum $1A_{pk}$ for less than 10ms duration has to be kept in mind, which is restricted by the maximum possible current through antiparallel protection diodes (see fig. 10a). This matters especially if attached circuitry is operated in a switched or pulsed mode, or, exposed to high-power radio frequency bursts (like in FT-ICR or NMR experiments).

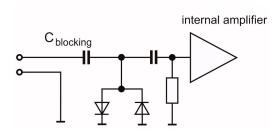


Figure: 10a
Input protection scheme (each channel)

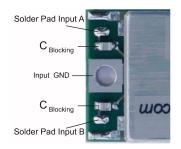


Figure: 10b

Location of removable blocking capacitors

In case the blocking capacitors are bridged, the input ESD-protection diodes limit the maximum voltage to about +/-750mV. Behind this protection circuitry the subsequent amplifier stages follow capacitively (AC) coupled.

Thermal Anchoring

Mounting the device into a cryogenic setup demands for a good thermal coupling, which is essential to achieve the specified performance of the CX-4 series amplifiers at low temperatures. The substrate, on which the circuitry is placed, should be connected by the user to an appropriate heat sink or cold finger. It is recommended to use a high conductance thermal agent like "Apiezon N" to provide a good heat flow between the adjacent surfaces (apply only as very *thin* layer, to bridge possible vacuum gaps). We recommend using one of the 3mm-holes for mounting with Brass or (preferably) Aluminium screws on a cold surface, or cold finger. Using Brass or Aluminium material (rather than other metals) is essential, since it will contract stronger than for instance steel or copper, which have a smaller thermal contraction when getting cold. Note that using stainless steel screws can drastically impair the thermal connection, due to thermal contraction mismatch (screws getting loose) and quite low thermal conduction at cryogenic temperatures.

When mounting the thermal connection, ensure to avoid mechanical tension of the remaining parts of the amplifier or other kind of mechanical stress. It is recommended, not to connect both amplifier ends with screws, unless the substrate to connect shows a similar thermal expansion like the amplifier's Aluminium (AlMg alloy) housing. Copper or Aluminium substrates serve well in this respect.

Commissioning in a Vacuum or Cryogenic Setup

After cleaning and baking (in case required, see also page 4) the CX-4 device can be mounted and wired up in a cryogenic vacuum chamber. It is very important to connect ground lines first for **ESD reasons** (fatal damage may occur by Electrostatic Discharge). The device may be checked for obvious mounting problems and eventually powered up with appropriate supply voltages (e.g. A3-5 Biasing Controller Unit).

Before power is applied to the device, one should carefully check the cable connections in order to avoid damage or malfunction. With a standard multimeter (DMM) one can perform a quick check of resistances. The following table lists typical terminal values of the amplifier lines versus GND.

| Line designator or Pad | Resistance vs. GND | Remark | |
|------------------------|--|---|--|
| G1A, G1B | 1.02 MΩ ± 0.02 MΩ | value slightly differs over 4K-300K range | |
| Output A, Output B | approx. $75\Omega \pm 15\Omega$ @ 300K | Since the device output features protection diod the value shown on a DMM display depends | |
| | approx. 48 Ω @ 4.2K | the measurement current and voltage in resistance measuring mode. | |

Table 3: typical resistance values of lines versus GND, measured with standard multimeter.

Cool-Down Procedure and Readjustments

After a complete check of the cabling (using a DMM in Ω -Mode, table above) and in case the latter is correct, one may temporarily power-up the device. The biasing currents on G1A, G1B are in the μ A range. The room temperature controller will adjust the voltage on G1A, G1B such that the supply

currents on the signal lines are around 1.6mA. During cool down in a cryostat the device **must** be switched off. The reason are strong offset shifts, which may cause temporary malfunctions otherwise. Please turn the power only on, once the final temperature is reached or temperature is already below 45K. After cooling down one may recheck the resistance of lines to be sure the device is operational. Note:

During cool-down/warm-up procedures always maintain a temperature rise or decrease of no more than +/-20 degrees Kelvin per minute. Note that exceeding this temperature slew/fall rate may damage the device due to formation of mechanical cracks. **Never apply thermal shocks to the device like dipping into a cryogenic liquid**.

Cool-Down and Warm-Up Cycles

Care has to be taken in the cool down and warm up phases. A fast drop into cryogenic liquids can **damage** the device because of excessive mechanical stress, caused by rapid thermal contractions or expansions. It is strongly recommended to keep the rate of temperature change below +/- 20K / minute. A complete cool down from room temperature into a cryogenic liquid like liquid Nitrogen or liquid Helium should take at least 20 minutes (liquid Helium) or 15 minutes (liquid Nitrogen).

Care has also to be taken, in case the device is brought from the cold state into normal air because of humidity condensing on the cold surfaces. In case the device is still powered up with supply voltages, a water film on the surfaces will lead to immediate destructive and possibly fatal galvanic corrosion. It is strongly recommended to let the device dry thoroughly before next operation, eventually using a conventional hair dryer, after the device was brought out of vacuum. Beware of overheating the device in this procedure. The use of so-called "hot air guns" is not allowed, since the latters air temperature easily exceeds 150 deg Celsius, which may lead to rapid overheating and substantial, non-reversible damage of the device. Even using conventional hair dryers, they should be set to minimum heat output and the device temperature carefully monitored in order to **never** exceed 150 deg. Celsius.

Temperature Check Diode

One of the soldering pads (see figure 2) is internally connected by a silicon diode to GND, by which the temperature of the device can be monitored. The diode should by biased with an electrical current of 5 to 7µA, and will display a voltage of around 0.7V at roomtemperature, 1.05V at 77K and approx. 1.35V at 4.2 Kelvin environmental temperature. The diode is not (explicitly) calibrated, but its voltage serves well to get a coarse estimate of the local temperature and helps finding thermal issues (e.g. heating up of the amplifier because of bad cooling inside a cryostat). Note that the 2-channel 'narrow-case' version does not have this feature, due to restricted space.

Amplification and Noise Data

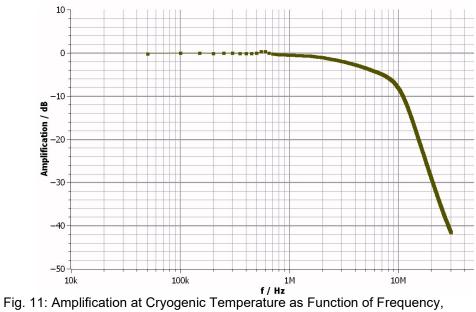


Fig. 11: Amplification at Cryogenic Temperature as Function of Frequency, expressed in dB relative to the amplification factor at f = 100kHz.

The data set comprises the cryogenic amplifier (at 5.6K) including the biasing section with 50 Ohm load.

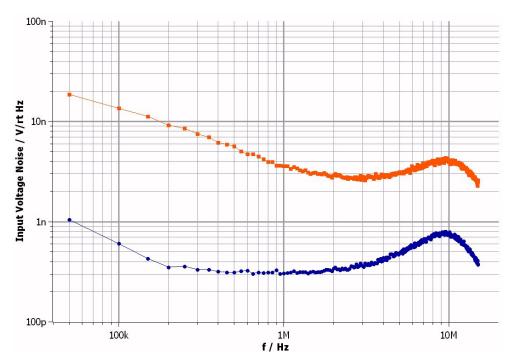


Fig. 12a: Input Voltage Noise Density at 300K and at 4.2K in a cryogenic vacuum chamber, frequency up to 20MHz (standard version of CX-4)

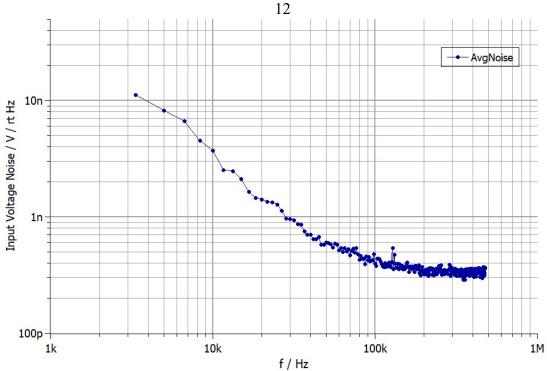


Fig. 12b: Input Voltage Noise Density at 6K, detailed lower frequency range 3kHz to 500kHz (standard version of CX-4)

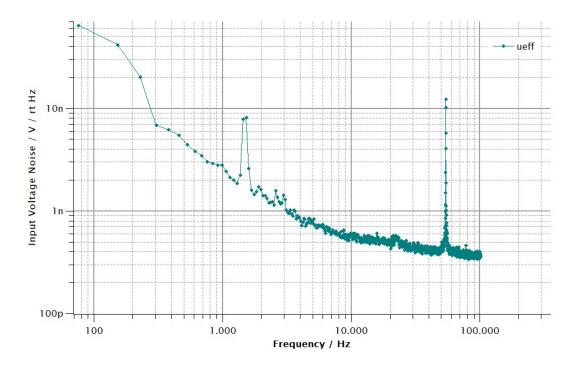


Fig. 12c: Input Voltage Noise Density at 6.5K, lower frequency range 70Hz to 100kHz, Low-Frequency version of CX-4. Note that peaks around 1.5kHz and 53kHz stem from external parasitic noise sources

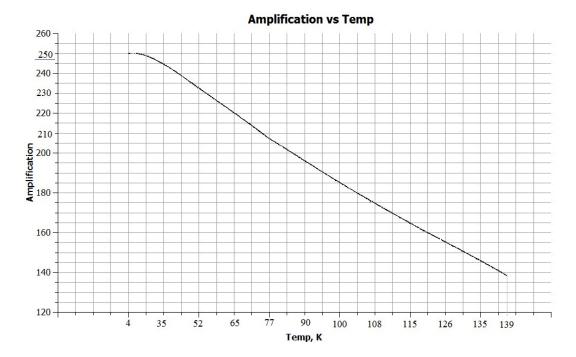


Fig. 13: Voltage Amplification factor as function of ambient temperature, from ~4.2K to elevated cryogenic temperatures, A = 250V/V amplification selected in this graph. The other amplification settings (600V/V, 1200V/V, 2400V/V) behave correspondingly.

Note, that the amplification labels on the A3-5 biasing box *only* refer to 4.2K operation.

The decrease of amplification at elevated temperatures as shown above is not automatically being corrected, since the nominal operating temperature is 4.2K.

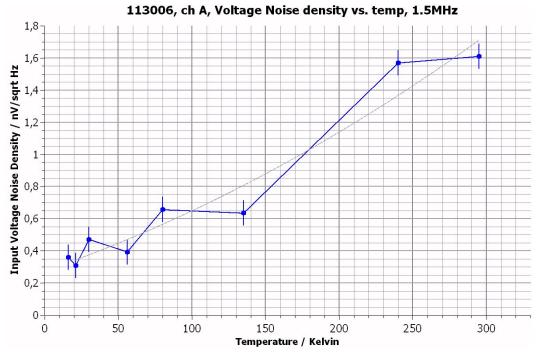


Fig. 14: Voltage Input Noise Density at f = 1.5MHz as function of ambient temperature

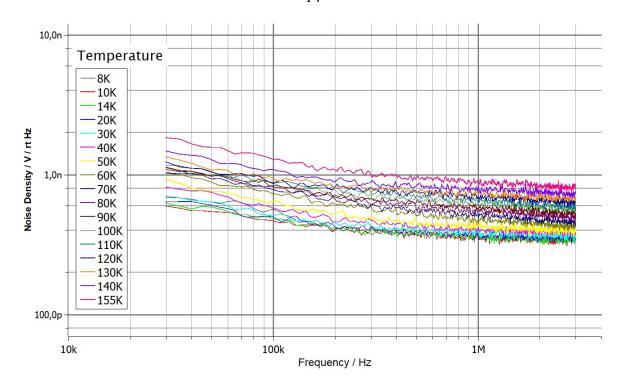


Fig. 15: Voltage Input Noise Density Graphs as function of ambient temperature from 8K to 155K. (standard version of CX-4)

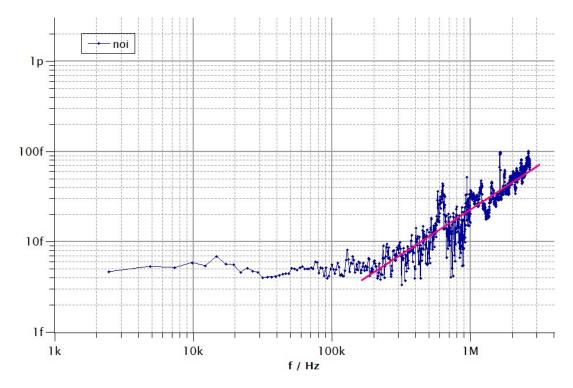


Fig. 16: Input Current Noise Density, standard version of CX-4, determined at T=5.8K. Unit on Y-axis: A/\sqrt{Hz} ; note that data points above 250kHz may be affected by interfering external noise sources during measurement (despite shielding). The pink line suggests a proportional f increase above approx. 300kHz.

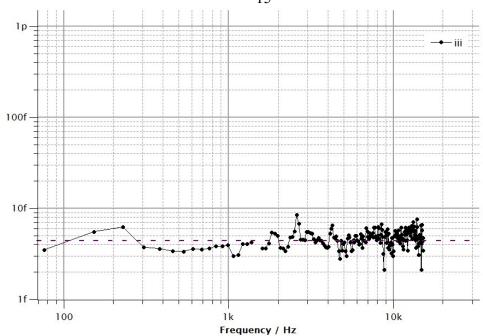


Fig. 17: Input Current Noise Density, low-frequency (LF) version of CX-4, determined at T=6K. Unit on Y-axis: A/ $\sqrt{\text{(Hz)}}$. The purple line suggests an average value of 4.5fA / rt Hz.

Geometrical Outline

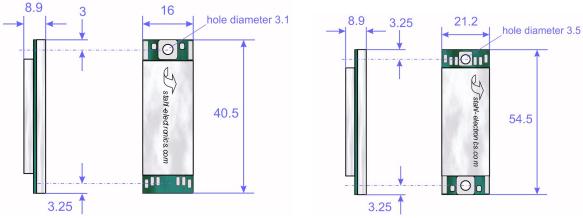


Figure 18a, b: Outline dimensions 1-channel version and 2-channel version (units: mm) with solder pads; note that figure 18a applies also to the narrow-case variant of the 2-channel version

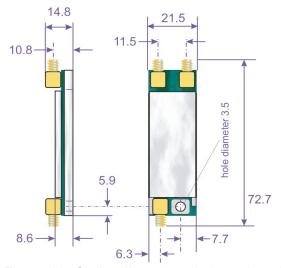


Figure 18c: Outline dimensions 1-channel version with SMA terminals

LED Indicator threshold values of A3-5 biasing controller

| | too low | ok | too high | remark |
|---|---------|-------------|----------|--|
| Output Line A and B (monitoring DC level) | < 0.2V | 0.2V 0.33V | >0.33V | |
| Supply Currents | < 1.0mA | 1.0mA 2.0mA | >2.0 mA | currents flow through A3-5 inputs and CX-4 outputs |

Table 4: typical DC threshold levels, defining the range in which individual LEDs will lighten up.

Trouble Shooting

In case not all LEDs show green light, there could be the following reasons.

DC level on Output line A or B too low:

- there could be a short from a cryogenic signal output line to GND or
- wrong biasing on the G1A or G1B line or Biasing not connected.

DC level on Output line A or B too high:

- may be caused by an open line (cable towards cryogenic amplifier interrupted and open) or wrong biasing on the G line.
- A missing GND connection (300K-to-cryogenic) could also be the reason.

DC level on an Output line too high and on the other too low:

- possibly G1A and G1B interchanged or the output lines interchanged (A \leftrightarrow B)

Supply current too low:

- biasing G too negative (maybe not in 'Auto-Mode', check switch position on controller)
- missing GND connection (300K to cryogenic)

Supply current too high:

- short cut from signal line to GND, or short cut from an output to GND
 - → disconnect cryogenic amplifier to prevent damage
- biasing G too positive (e.g. during manual operation, PID disabled)
- biasing line G not connected at all or shorted to GND

If one of these error conditions occurs, check carefully all connections, eventually also the nominal resistances of the supply lines to the cryogenic amplifier according to the value listed above. Note that in case the cryogenic amplifier is operated at room temperature, the regulation loop may not lock due to occurrence of leakage currents. This problem will disappear as soon as the amplifier is cooled down substantially below 0°C. Please note that the amplifier must be **switched off during the cool-down process**, until final temperature is reached. Otherwise the PID regulation loop may have problems to stabilize the working point. If one assumes, that the power was accidentally turned on during cooling, one can restore the correct operating condition by warming up completely to 300K and starting again in the off-state (non-powered).

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